

### Snubberless™, logic level and standard 8 A Triacs

#### **Features**

- Medium current Triac
- High static and dynamic commutation
- Low thermal resistance with clip bonding
- Packages is RoHS (2002/95/EC) compliant
- 600 V V<sub>RM</sub>
- UL certified (ref. file E81734)

#### **Applications**

- Value sensitive application
- General purpose ac line load switching
- Motor control circuits in power tools
- Small home appliances, lighting
- Inrush current limiting circuits
- Overvoltage crowbar protection

#### **Description**

Available in through-hole, the T8T series of Triacs can be used as on/off or phase angle control function in general purpose ac switching where high commutation capability is required.

This series can be designed-in in many value sensitive appliances thanks to the parameters guidance provided in the following pages.

Provides insulation rated at 2500 V rms (TO-220AB insulated package).

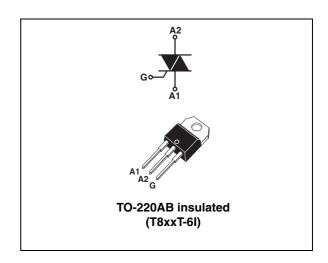


Table 1. Device summary

Table II Device culturally					
Order code	Symbol	Value			
T810T-6I	I <sub>GT</sub> 3Q logic level	10 mA			
T820T-6I T835T-6I	I <sub>GT</sub> 3Q Snubberless	20 / 35 mA			
T825T-6I	I <sub>GT</sub> 4Q standard	25 mA			

TM: Snubberless is a trademark of STMicroelectronics

Characteristics T8T

### 1 Characteristics

Table 2. Absolute ratings (limiting values;  $T_j = 25$  °C, unless otherwise specified)

Symbol	Parameter	Value	Unit		
I <sub>T(RMS)</sub>	On-state rms current (full sine wave) $T_c = 97$ °C			8	Α
	Non repetitive surge peak on-state current	F = 50 Hz	t <sub>p</sub> = 20 ms	60	Α
ITSM	(full cycle, T <sub>j</sub> initial = 25 °C)	F = 60 Hz	$t_p = 16.7 \text{ ms}$	63	А
l <sup>2</sup> t	$l^2t$ Value for fusing $t_p = 10 \text{ ms}$			26	A <sup>2</sup> s
dl/dt	Critical rate of rise of on-state current $I_G = 2 \times I_{GT}$ $F = 60 \text{ F}$		T <sub>j</sub> = 125 °C	50	A/μs
V <sub>DSM</sub> / V <sub>RSM</sub>	Non repetitive surge peak off-state voltage $t_p = 10 \; \text{ms}$		T <sub>j</sub> = 25 °C	V <sub>DRM</sub> /V <sub>RRM</sub> + 100	V
I <sub>GM</sub>	Peak gate current $t_p = 20 \mu s$ $T_j$		T <sub>j</sub> = 125 °C	4	Α
P <sub>G(AV)</sub>	Average gate power dissipation $T_j = 125  ^{\circ}\text{C}$				W
T <sub>stg</sub>	Storage junction temperature range			- 40 to + 150	°C
T <sub>j</sub>	Operating junction temperature range			- 40 to + 125	°C

T8T Characteristics

Table 3. Electrical characteristics ( $T_j = 25$  °C, unless otherwise specified)

Cumbal	Test conditions	Quadrant		T8xxT			l l	
Symbol	Test conditions	Quadrant		T810T	T820T	T825T	T835T	Unit
I <sub>GT</sub> <sup>(1)</sup>	$V_D = 12 \text{ V}, R_L = 30 \Omega$	1 - 11 - 111	MAX.	10	20	25	35	mA
'GT \"		IV				40		
V <sub>GT</sub>	$V_D = V_{DRM}, R_L = 30 \Omega,$ $T_j = 25  ^{\circ}C$	ALL	MAX.	1.3		V		
V <sub>GD</sub>	$V_D = V_{DRM}$ , $R_L = 3.3 \text{ k}\Omega$ , $T_j = 125 \text{ °C}$	ALL	MIN.	0.2		V		
I <sub>H</sub> <sup>(2)</sup>	I <sub>T</sub> = 500 mA		MAX.	15	25	30	40	mA
	I <sub>G</sub> = 1.2 I <sub>GT</sub>	I - III		20	35	40	50	
IL		IV	MAX.			40		mA
		II		25	40	70	70	
dV/dt (2)	V = 67% V gate open	T <sub>j</sub> = 125 °C	MIN.	100	750	500	2000	V/µs
uv/ut · /	$V_D = 67\% V_{DRM,}$ gate open	$T_j = 150  {}^{\circ}C^{(3)}$	IVIIIN.	50	500	300	1000	v/µS
	$(dV/dt)c = 0.1 V/\mu s$			5.4				
	$(dV/dt)c = 10 V/\mu s$	T <sub>j</sub> = 125 °C		2		4.5		
(di/dt)c (2)	Without snubber		MIN.		3.4		8	A/ms
(ui/ut)c · /	$(dV/dt)c = 0.1 V/\mu s$		IVIIIV.	2.5				7/1113
	(dV/dt)c = 10 V/μs	$T_j = 150  {}^{\circ}C^{(3)}$		1		2		
	Without snubber				2		6.5	

- 1. Minimum  $I_{\mbox{\footnotesize{GT}}}$  is guaranted at 5% of  $I_{\mbox{\footnotesize{GT}}}$  max.
- 2. For both polarities of A2 referenced to A1.
- 3. Derating information for excess temperature above  $\mathbf{T}_{j}\,\text{max}.$

Table 4. Static characteristics

Symbol	Test conditions				Unit
V <sub>T</sub> <sup>(1)</sup>	$I_{TM} = 11.3 \text{ A}, t_p = 380  \mu\text{s}$	T <sub>j</sub> = 25 °C	MAX.	1.60	V
V <sub>TO</sub> <sup>(1)</sup>	Threshold voltage	T <sub>j</sub> = 125 °C	MAX.	0.87	V
R <sub>D</sub> <sup>(1)</sup>	Dynamic resistance	T <sub>j</sub> = 125 °C	MAX.	60	mΩ
	$V_{DRM} = V_{RRM}$	T <sub>j</sub> = 25 °C	MAX.	5	μΑ
I <sub>DRM</sub>		T <sub>j</sub> = 125 °C		1	0
IRRM	$V_D = 0.9 \times V_{DRM}$	T <sub>j</sub> = 150 °C <sup>(2)</sup>	TYP.	1.9	mA

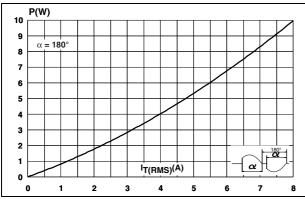
- 1. For both polarities of A2 referenced to A1.
- 2. Derating information for excess temperature above  $T_{i}$  max.

**Characteristics T8T** 

Table 5. Thermal resistance

Symbol	Parameter	Value	Unit
R <sub>th(j-c)</sub>	Junction to case (AC)	2.8	°C/W
R <sub>th(j-a)</sub>	Junction to ambient (DC)	60	°C/W

On-state rms current versus case Maximum power dissipation versus Figure 2. Figure 1. rms on-state current temperature



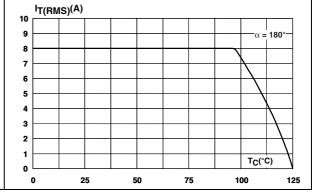
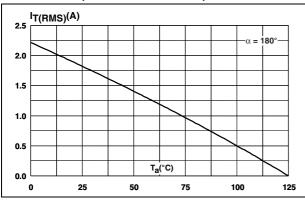


Figure 3. On-state rms current versus ambient temperature (free air convection)

Figure 4. **Relative variation of thermal** impedance versus pulse duration



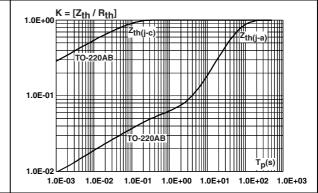


Figure 5. **On-state characteristics** (maximum values)

number of cycles I<sub>TM</sub>(A) ITSM(A) 70 60 Non repetitive T<sub>j</sub> initial = 25 °C 50 40 30 Repetitive  $T_C = 97 \,^{\circ}C$ 20 T<sub>j</sub>max: V<sub>to</sub> = 0.87 V 10  $R_d = 6.0 \text{ m}\Omega$ Number of cvo  $V_{TM}(V)$ 0 100

Figure 6. Surge peak on state current versus

100

10

**T8T Characteristics** 

Non repetitive surge peak on-state Figure 8. Relative variation of gate trigger Figure 7. current and gate trigger voltage current for a sinusoidal versus junction temperature

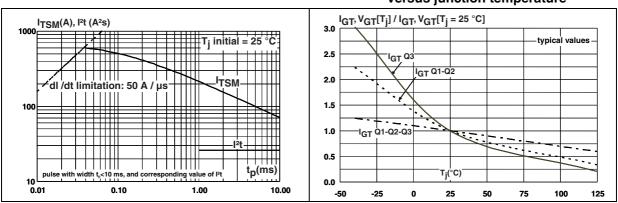


Figure 9. Relative variation of holding current and latching current versus junction temperature

Figure 10. Relative variation of static dV/dt immunity versus junction temperature

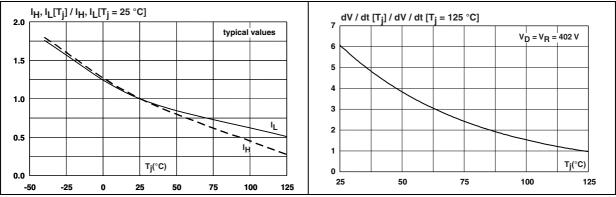
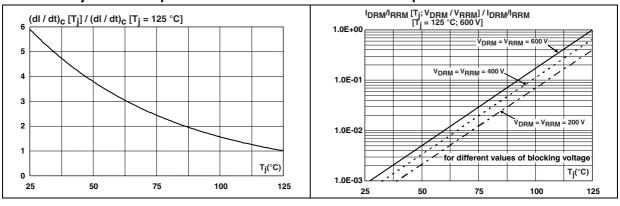


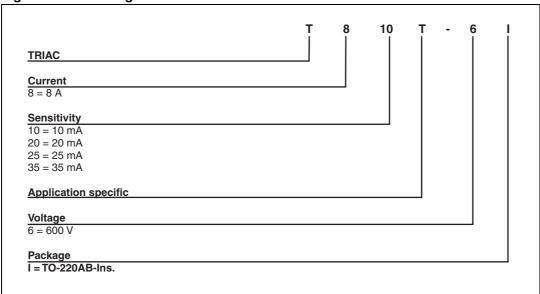
Figure 11. decrease of main current versus junction temperature

Relative variation of critical rate of Figure 12. Relative variation of leakage current versus junction temperature



# 2 Ordering information scheme

Figure 13. Ordering information scheme

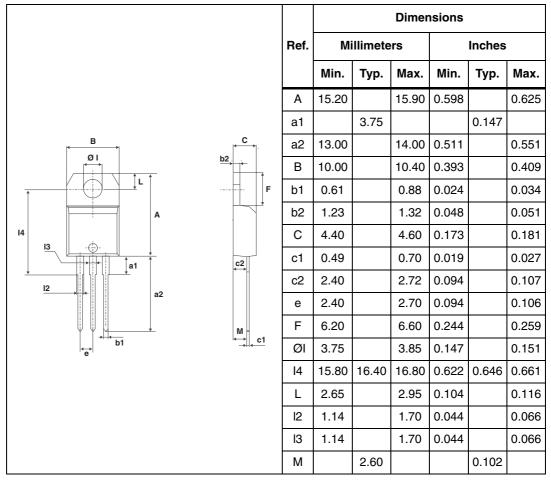


#### 3 Package mechanical data

- Epoxy meets UL94, V0
- Lead-free packages

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: <a href="https://www.st.com">www.st.com</a>. ECOPACK<sup>®</sup> is an ST trademark.

Table 6. TO-220AB Insulated dimensions



Ordering information T8T

# 4 Ordering information

Table 7. Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
T810T-6I	T810T-6I				
T820T-6I	T820T-6I	TO-220AB-Ins.	2.3 g	50	Tube
T825T-6I	T825T-6I	10-220AB-IIIs.	2.5 g	50	Tube
T835T-6I	T835T-6I				

# 5 Revision history

Table 8. Document revision history

Date	Revision	Changes
10-Sep-2009	1	First issue.
18-Jan-2010	2	Updated pag.1.
20-Sep-2011	3	Updated: Features.

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